

Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION <i>(Use several sheets if necessary)</i>		Docket Number (Optional) 4308.4US (99-1199.04/US)		Application Number 10/791400	
		Applicant John T. Moore			
		Filing Date March 2, 2004		Group Art Unit 2824	

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
CW	5,567,638	10/1996	Lin et al.	438	592	
	5,633,177	05/1997	Anjum	438	301	
	6,013,553	01/2000	Wallace et al.	438	287	
	6,017,808	01/2000	Wang et al.	438	528	
	6,136,654	10/2000	Kraft et al.	438	287	
	6,140,024	10/2000	Misium et al.	430	314	
	6,251,761	06/2001	Rodder et al.	438	591	
	6,261,973	07/2001	Misium et al.	438	775	
	6,342,437	01/2002	Moore	438	474	
	CW	6,528,396	03/2003	Moore	438	484

FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS		(Including Author, Title, Date, Pertinent Pages, Etc.)
CW		Al-Shareef et al., "Device Performance of <i>in situ</i> Steam Generated Gate Dielectric Nitrided by Remote Plasma Nitridation", Applied Physics Letters, Volume 78, Number 24, June 11, 2001, pps. 3875-3877.
		Al-Shareef et al., "Plasma Nitridation of Very Thin Gate Dielectrics", Microelectronic Engineering, 59, 2001, pps 317-322.
CW		Hattangady et al., "Ultrathin Nitrogen-Profile Engineered Gate Dielectric Films", IEDM Tech. Dig., 1996, pps. 495-498.

EXAMINER Christian Wilson	DATE CONSIDERED 9/8/04
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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OTHER DOCUMENTS		(Including Author, Title, Date, Pertinent Pages, Etc.)
<div style="border: 1px solid black; padding: 2px; width: 50px; height: 30px; margin: 0 auto;"> </div>		Koh et al., "Plasma-Engineered Si-SiO ₂ Interfaces: Monolayer Nitrogen Atom Incorporation by Low-Temperature Remote Plasma-Assisted Oxidation in N ₂ O", Surface and Coatings Technology, 1998; pps. 1524-1528.
<div style="border: 1px solid black; padding: 2px; width: 50px; height: 30px; margin: 0 auto;"> </div>		Lucovsky et al., "Plasma Processed Ultra-Thin SiO ₂ Interfaces for Advanced Silicon NMOS and PMOS Devices: Applications to Si-Oxide/Si Oxynitride, Si-Oxide/Si Nitride and Si-Oxide/ Transition Metal Oxide Stacked Gate Dielectrics", Thin Solid Films, 2000, pps. 217-227.
<div style="border: 1px solid black; padding: 2px; width: 50px; height: 30px; margin: 0 auto;"> </div>		Mehrotra et al., "A 1.2V, Sub-0.09µm Gate Length CMOS Technology", IEDM Tech. Dig., 1999, pps. 419-422.
<div style="border: 1px solid black; padding: 2px; width: 50px; height: 30px; margin: 0 auto;"> </div>		Niimi et al., "Monolayer-Level Controlled Incorporation of Nitrogen in Ultrathin Gate Dielectrics Using Remote Plasma Processing: Formation of Stacked "N-O-N" Gate Dielectrics", J. Vac. Sci. Technology B 17, Nov/Dec 1999, pps. 2610-2621.
<div style="border: 1px solid black; padding: 2px; width: 50px; height: 30px; margin: 0 auto;"> </div>		Ting et al., "The Effect of Remote Plasma Nitridation on the Integrity of the Ultrathin Gate Dielectric Films in 0.13 µm CMOS Technology and Beyond", IEEE Electron Device Letters, Vol. 22, No. 7, July 2001, pps. 327-329.

EXAMINER <div style="border: 1px solid black; padding: 5px; margin-top: 5px;"> </div>	DATE CONSIDERED <div style="border: 1px solid black; padding: 5px; margin-top: 5px;"> </div>
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